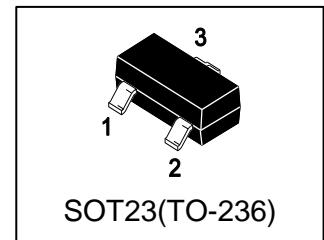


L2N7002SLLT1G

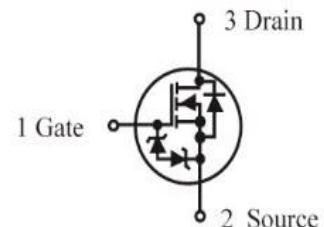
S-L2N7002SLLT1G

Small Signal MOSFET
380 mAmps, 60V N-Channel SOT-23



1. FEATURES

- We declare that the material of product compliance with RoHS requirements and Halogen Free.
- S- prefix for automotive and other applications requiring unique site and control change requirements; AEC-Q101 qualified and PPAP capable.
- ESD protected
- Low RDS(on)



2. APPLICATIONS

- Low side load switch
- Level shift circuits
- DC-DC converter
- Portable applications i.e. DSC, PDA, Cell Phone, etc.

3. DEVICE MARKING AND ORDERING INFORMATION

Device	Marking	Shipping
L2N7002SLLT1G	701	3000/Tape&Reel
L2N7002SLLT3G	701	10000/Tape&Reel

4. MAXIMUM RATINGS($T_a = 25^\circ C$)

Parameter	Symbol	Limits	Unit
Drain-Source Voltage	VDSS	60	V
Gate-Source Voltage	VGS	± 20	V
Drain Current – Steady State – t<5s	ID	320 230 380 270	mA
Pulsed Drain Current ($t_p=10\mu s$)	IDM	1.5	A
Source Current (Body Diode)	IS	300	mA

5. THERMAL CHARACTERISTICS

Parameter	Symbol	Limits	Unit
Total Device Dissipation(Note 1) – Steady State – t<5s	PD	300 420	mW
Junction-to-Ambient(Note 1) – Steady State – t<5s	R _{θJA}	417 300	°C/W
Lead Temperature for Soldering Purposes (1/8 " from case for 10 s)	TL	260	°C
Junction and Storage temperature	T _{J,Tstg}	-55~+150	°C
Gate-Source ESD Rating(HBM, Method 3015)	ESD	2000	V

6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)

OFF CHARACTERISTICS

Characteristic	Symbol	Min.	Typ.	Max.	Unit
Drain–Source Breakdown Voltage (VGS = 0, ID = 250μA)	V _{BRDSS}	60	-	-	V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{BRDSS/TJ}	-	71	-	mV/°C
Zero Gate Voltage Drain Current TJ = 25°C (VGS = 0, VDS = 60 V) TJ = 125°C (VGS = 0, VDS = 50 V) TJ = 25°C	ID _{SS}	-	-	1.0	μA
		-	-	500	
		-	-	100	nA
Gate–Body Leakage Current, Forward (VGS = 20 V)	I _{GSSF}	-	-	10	μA
Gate–Body Leakage Current, Reverse (VGS = - 20 V)	I _{GSRR}	-	-	-10	μA

ON CHARACTERISTICS (Note 2)

Gate Threshold Voltage (VDS = VGS, ID = 250μA)	V _{GS(th)}	1.0	-	2.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)/TJ}	-	4	-	mV/°C
Static Drain–Source On–State Resistance (VGS = 10 V, ID = 500 mA) (VGS = 4.5 V, ID = 200 mA)	R _{D(on)}	-	-	2.8 3.2	Ω
Forward Transconductance (VDS = 5.0 V, ID = 200 mA)	g _{fs}	80	-	-	mS

DYNAMIC CHARACTERISTICS

Input Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	C _{iss}	-	-	35	pF
Output Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	C _{oss}	-	-	10	pF
Reverse Transfer Capacitance (VDS = 25 V, VGS = 0, f = 1.0 MHz)	C _{rss}	-	-	5	pF
Total Gate Charge	V _{GS} = 4.5 V, V _D = 10 V; ID = 500 mA	Q _{G(TOT)}	-	0.44	-
Gate-to-Source Charge		Q _{GS}	-	0.2	-
Gate-to-Drain Charge		Q _{GD}	-	0.1	-
Gate Resistance (VDS = 0 V, VGS = 0 V, f = 1.0 MHz)	R _g	-	30	-	kΩ

6. ELECTRICAL CHARACTERISTICS (Ta= 25°C)(Con.)

SWITCHING CHARACTERISTICS

Turn-On Delay Time	VDS = 30 V, VGEN = 10 V, ID = 500 mA, RG = 25Ω , RL = 60Ω	td(on)	-	20	-	ns
Rise Time		tr	-	55	-	
Turn-Off Delay Time		td(off)	-	200	-	
Fall Time		tf	-	180	-	

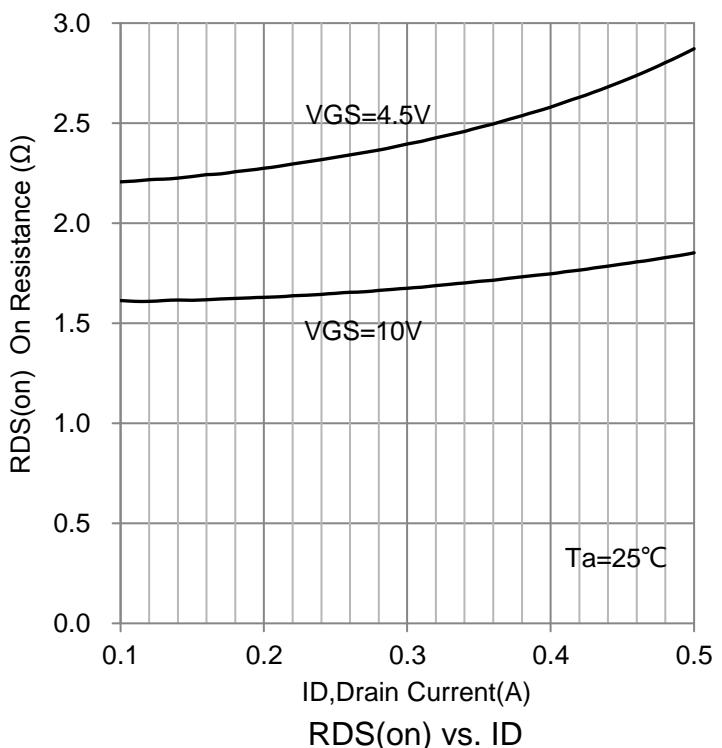
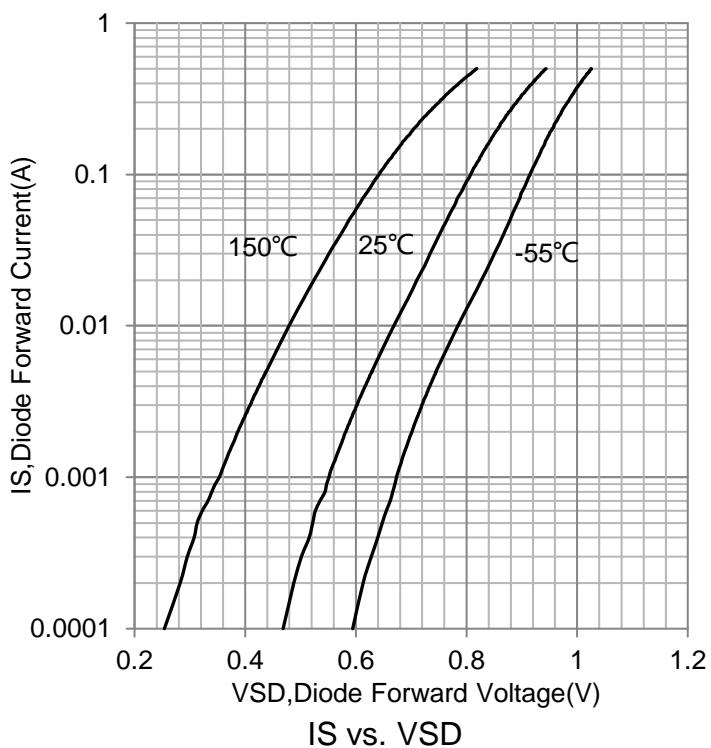
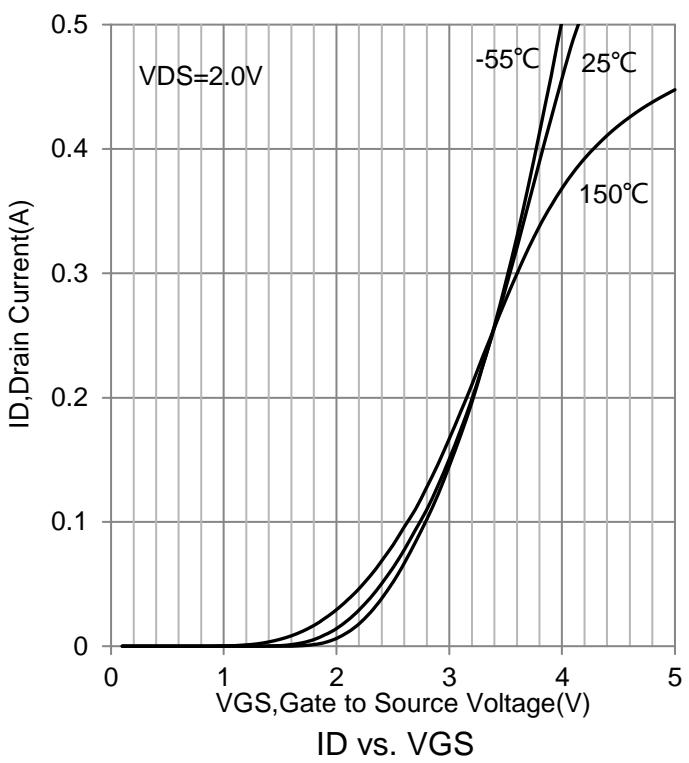
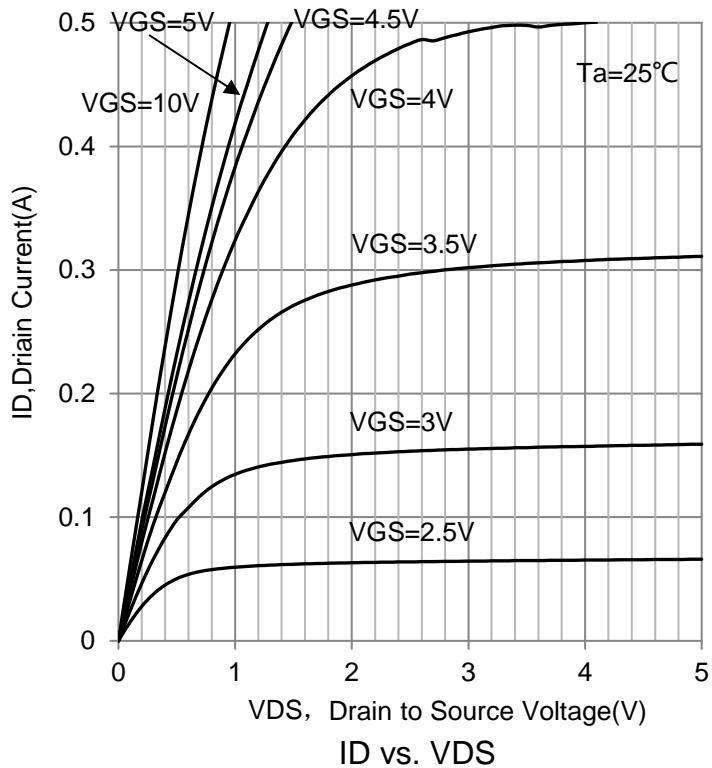
BODY-DRAIN DIODE RATINGS

Diode Forward On-Voltage (IS = 0.5A, VGS = 0 V)	VSD	-	0.85	-	V
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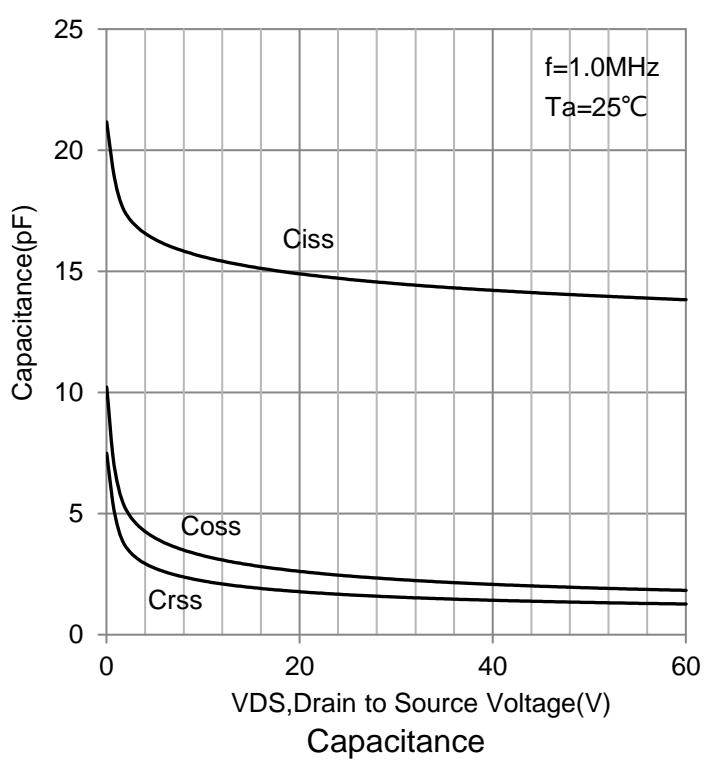
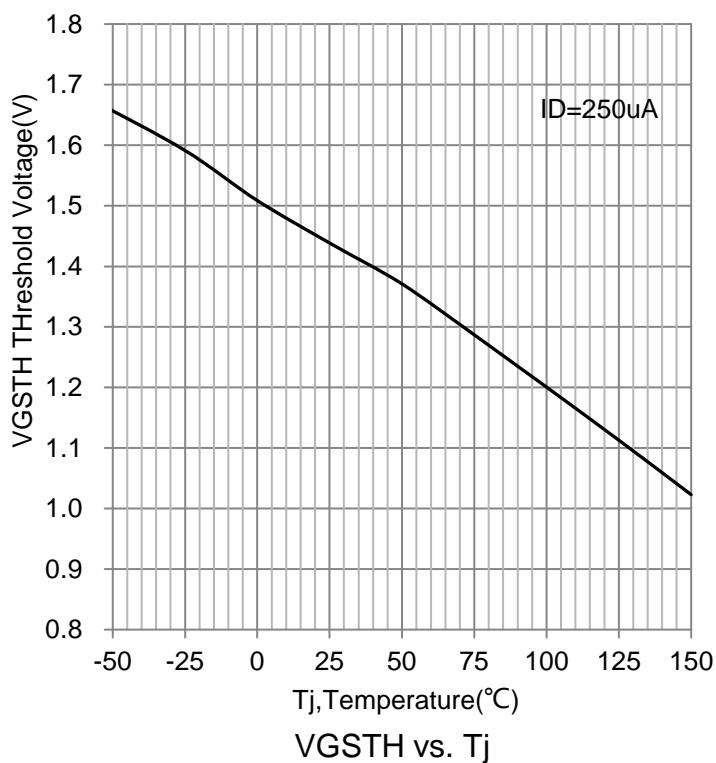
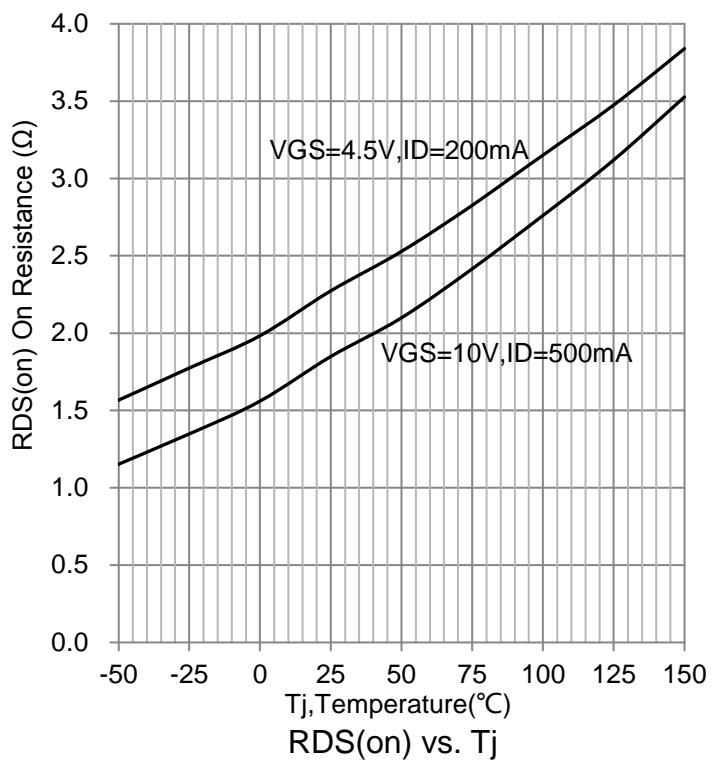
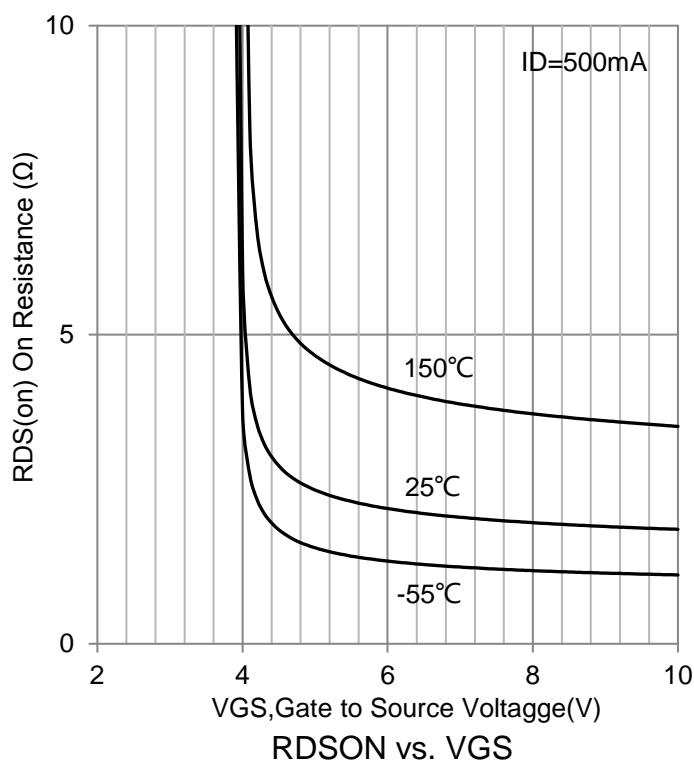
1. FR-4 = 1.0×0.75×0.062 in.

2. Pulse Test: Pulse Width ≤300 μs, Duty Cycle ≤2.0%.

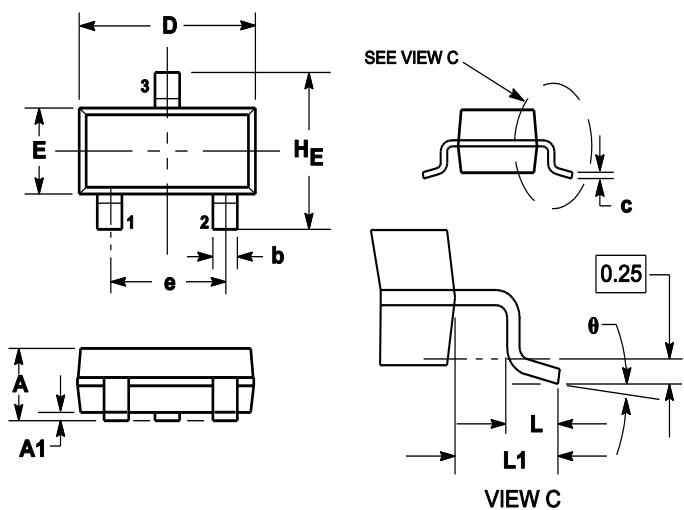
7. ELECTRICAL CHARACTERISTICS CURVES



7. ELECTRICAL CHARACTERISTICS CURVES(Con.)



8.OUTLINE AND DIMENSIONS

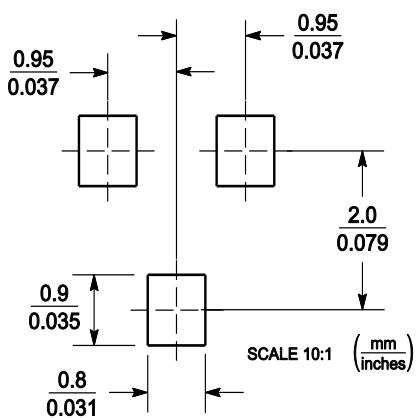


Notes:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.89	1	1.11	0.035	0.04	0.044
A1	0.01	0.06	0.1	0.001	0.002	0.004
b	0.37	0.44	0.5	0.015	0.018	0.02
c	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.9	3.04	0.11	0.114	0.12
E	1.20	1.3	1.4	0.047	0.051	0.055
e	1.78	1.9	2.04	0.07	0.075	0.081
L	0.10	0.2	0.3	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
H_E	2.10	2.4	2.64	0.083	0.094	0.104
θ	0°	---	10°	0°	---	10°

9.SOLDERING FOOTPRINT



DISCLAIMER

- Curve guarantee in the specification. The curve of test items with electric parameter is used as quality guarantee.
The curve of test items without electric parameter is used as reference only.
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- All information contained in this document is current as of the issuing date and subject to change without any prior notice. Before purchasing or using LRC's Products, please confirm the latest information with a LRC sales representative.